

In the claims:

1-41 (canceled)

42. (currently amended) A semiconductor wafer which comprises:

a plurality of integrated circuits, each of said integrated circuits separated from the other of said integrated circuits by a scribe region at the periphery of each said integrated circuit; each of said integrated circuits including:

a centrally disposed core region;

at least one bond pad disposed between said core region and said scribe region;

~~an~~ at least one electrostatic discharge device disposed between one said bond pad and extending at least partially beneath said bond pad; and

an I/O buffer extending unimpeded from ~~disposed between~~ said scribe region ~~and~~ to said core region and disposed laterally of said bond pad and said electrostatic discharge device relative to said core region and said scribe region.

43. (currently amended) A semiconductor The wafer of claim 42, wherein which comprises:

~~a plurality of integrated circuits, each of said integrated circuits separated from the other of said integrated circuits by a scribe region at the periphery of each said integrated circuit; each of said integrated circuits including:~~

~~a centrally disposed core region;~~

~~at least one bond pad disposed between said core region and said scribe region;~~

~~an~~ said electrostatic discharge device is disposed at least partially beneath said bond pad; and

~~an I/O buffer disposed between said scribe region and said core region.~~

44-48 (canceled)

49. (currently amended) A method of fabricating a semiconductor wafer which comprises the steps of:

providing a plurality of integrated circuits, each of said integrated circuits separated from the other of said integrated circuits by a scribe region at the periphery of each said integrated circuit; and providing in each of said integrated circuits:

a centrally disposed core region;

at least one bond pad disposed between said core region and said scribe region;

~~an~~ at least one electrostatic discharge device disposed between one said bond pad and extending at least partially beneath said bond pad; and

an I/O buffer extending unimpeded from ~~disposed between~~ said scribe region ~~and to said core region and disposed laterally of said bond pad and said electrostatic discharge device relative to said core region and said scribe region.~~

50-53 (canceled)